

Monolithic Dual Switching Diode Common Cathode

● FEATURES

- 1) We declare that the material of product compliant with RoHS requirements and Halogen Free.
- 2) S- Prefix for automotive and other applications requiring unique site and control change requirements; AEC-Q101 qualified and PPAP capable.

● DEVICE MARKING AND ORDERING INFORMATION

Device	Marking	Shipping
LBAV70LT1G	A4	3000/Tape&Reel
LBAV70LT3G	A4	10000/Tape&Reel

● MAXIMUM RATINGS($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Limits	Unit
Reverse Voltage	V_R	70	Vdc
Forward Current	I_F	200	mAdc
Peak Forward Surge Current	$I_{FM(surge)}$	500	mAdc

● THERMAL CHARACTERISTICS

Parameter Symbol	Symbol	Max.	Unit
Total Device Dissipation FR-5 Board(Note 1) $T_A = 25^\circ\text{C}$	P_D	225	mW
Derate above 25°C		1.8	mW/ $^\circ\text{C}$
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	556	$^\circ\text{C/W}$
Total Device Dissipation Alumina Substrate(Note 2) $T_A = 25^\circ\text{C}$	P_D	300	mW
Derate above 25°C		2.4	mW/ $^\circ\text{C}$
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	417	$^\circ\text{C/W}$
Junction and Storage Temperature	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$

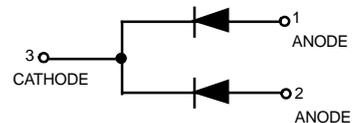
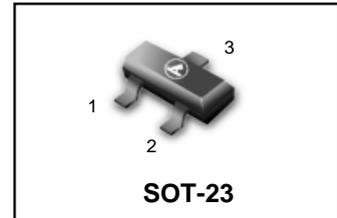
● ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Min	Max.	Unit
Reverse Breakdown Voltage($I_{(BR)}=100\mu\text{A}$)	$V_{(BR)}$	70	—	Vdc
Reverse Voltage Leakage Current ($V_R = 25\text{ Vdc}, T_J = 150^\circ\text{C}$)	I_R	—	60	uAdc
($V_R = 70\text{ Vdc}$)		—	2.5	
($V_R = 70\text{ Vdc}, T_J = 150^\circ\text{C}$)		—	100	
Diode Capacitance ($V_R = 0, f = 1.0\text{ MHz}$)	C_D	—	1.5	pF
Forward Voltage ($I_F = 1.0\text{ mAdc}$)	V_F	—	715	mVdc
($I_F = 10\text{ mAdc}$)		—	855	
($I_F = 50\text{ mAdc}$)		—	1000	
($I_F = 150\text{ mAdc}$)		—	1250	
Reverse Recovery Time (Figure 1) $I_F=I_R=10\text{ mAdc}, i_{R(REC)}=1.0\text{ mAdc}, R_L=100\ \Omega$	trr	—	6	ns

1. FR-5 = $1.0 \times 0.75 \times 0.062\text{ in.}$

2. Alumina = $0.4 \times 0.3 \times 0.024\text{ in.}$ 99.5% alumina.

LBAV70LT1G S-LBAV70LT1G



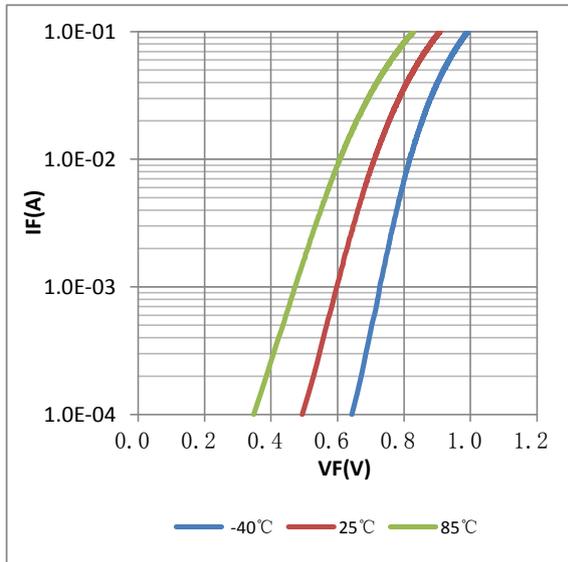
LBAV70LT1G, S-LBAV70LT1G
ELECTRICAL CHARACTERISTIC CURVES


FIG. 1 Forward Characteristics

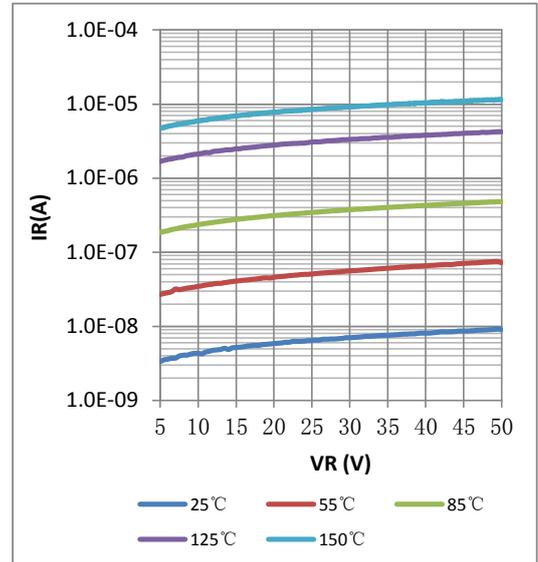


FIG. 2 Reverse Characteristics

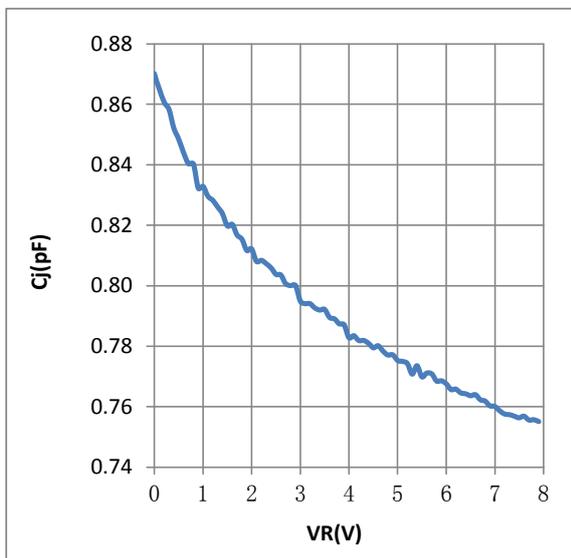
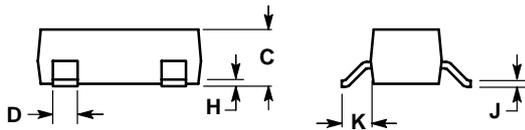
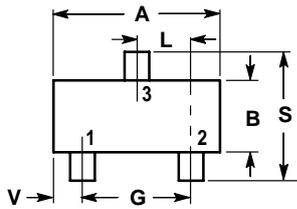


FIG. 3 Capacitance

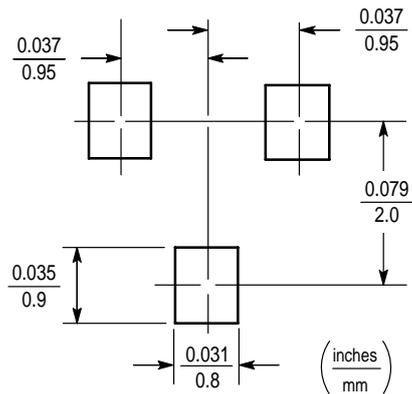
LBAV70LT1G, S-LBAV70LT1G

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NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.1102	0.1197	2.80	3.04
B	0.0472	0.0551	1.20	1.40
C	0.0350	0.0440	0.89	1.11
D	0.0150	0.0200	0.37	0.50
G	0.0701	0.0807	1.78	2.04
H	0.0005	0.0040	0.013	0.100
J	0.0034	0.0070	0.085	0.177
K	0.0140	0.0285	0.35	0.69
L	0.0350	0.0401	0.89	1.02
S	0.0830	0.1039	2.10	2.64
V	0.0177	0.0236	0.45	0.60



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